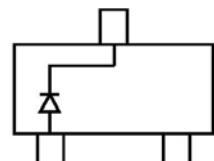
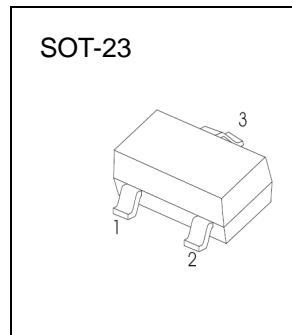


## SOT-23 Plastic-Encapsulate Diodes

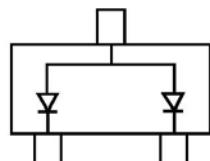
BAS40/-04/-05/-06 SCHOTTKY BARRIER DIODE

**FEATURES**

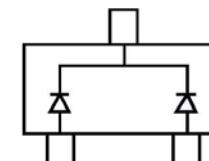
- Low Forward Voltage
- Fast Switching



BAS40 MARKING: 43

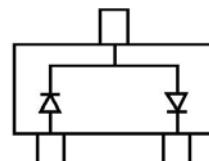


BAS40-06 MARKING: 46



BAS40-05 MARKING

45



BAS40-04 MARKING

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Maximum Ratings @Ta =25°C

Parameter	Symbol	Limit	Unit
Peak repetitive peak reverse voltage	V <sub>RRM</sub>		
Working peak reverse voltage	V <sub>RWM</sub>	40	V
DC blocking voltage	V <sub>R</sub>		
Forward continuous current	I <sub>FM</sub>	200	mA
Power dissipation	P <sub>D</sub>	200	mW
Thermal resistance junction to ambient	R <sub>θJA</sub>	500	°C/W
Junction temperature	T <sub>J</sub>	15	°C
Storage temperature range	T <sub>STG</sub>	-55~+150	°C

**ELECTRICAL CHARACTERISTICS (Ta=25 unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V <sub>(BR)</sub>	I <sub>R</sub> = 10μA	40		V
Reverse voltage leakage current	I <sub>R</sub>	V <sub>R</sub> =30V		200	nA
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =1mA I <sub>F</sub> =40mA		380 1000	mV
Diode capacitance	C <sub>D</sub>	V <sub>R</sub> =0,f=1MHz		5	pF
Reverse recovery time	t <sub>rr</sub>	I <sub>rr</sub> =1mA, I <sub>R</sub> =I <sub>F</sub> =10mA R <sub>L</sub> =100Ω		5	ns

